

Paul Berger

List of Publications by Year in descending order

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188
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3,096
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186265

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193
docs citations

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times ranked

2754
citing authors

#	ARTICLE	IF	CITATIONS
1	Flexible, solution-processed, indium oxide (In ₂ O ₃) thin film transistors (TFT) and circuits for internet-of-things (IoT). Materials Science in Semiconductor Processing, 2022, 139, 106354.	4.0	15
2	Selective atomic layer deposition on flexible polymeric substrates employing a polyimide adhesive as a physical mask. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 012405.	2.1	6
3	Foreword Special Issue on Low-Temperature Processing of Electronic Materials for Cutting Edge Devices. IEEE Transactions on Electron Devices, 2021, 68, 3138-3141.	3.0	0
4	Temperature Characterization of Unipolar-Doped Electroluminescence in Vertical GaN/AlN Heterostructures. Energies, 2021, 14, 6654.	3.1	0
5	Flexible, Gallium Oxide (Ga ₂ O ₃) Thin Film Transistors (TFTs) and Circuits for the Internet of Things (IoT). , 2021, , .		2
6	Flexible Thin Film Transistor (TFT) and Circuits for Internet of Things (IoT) based on Solution Processed Indium Gallium Zinc Oxide (IGZO). , 2021, , .		0
7	Electroluminescence in Unipolar-Doped $\text{In}_{0.53}\text{Ga}_{0.47}\text{N}$ Resonant-Tunneling Diodes: A Competition between Interband Tunneling and Impact Ionization. Physical Review Applied, 2021, 16, .	3.8	11
8	Investigation of Switching Time in GaN/AlN Resonant Tunneling Diodes by Experiments and P-SPICE Models. IEEE Transactions on Electron Devices, 2020, 67, 75-79.	3.0	12
9	0.7-GHz Solution-Processed Indium Oxide Rectifying Diodes. IEEE Transactions on Electron Devices, 2020, 67, 360-364.	3.0	8
10	RTD Light Emission around 1550 nm with IQE up to 6% at 300 K. , 2020, , .		2
11	Effects of growth temperature on electrical properties of GaN/AlN based resonant tunneling diodes with peak current density up to 1.01 MA/cm ² . AIP Advances, 2020, 10, .	1.3	7
12	Superior growth, yield, repeatability, and switching performance in GaN-based resonant tunneling diodes. Applied Physics Letters, 2020, 116, .	3.3	22
13	Dependence of growth temperature on the electrical properties and microstructure of MBE-grown AlN/GaN resonant tunneling diodes on sapphire. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, 032214.	1.2	4
14	0.6V Threshold Voltage Thin Film Transistors With Solution Processable Indium Oxide (In ₂ O ₃) Channel and Anodized High- κ Al ₂ O ₃ Dielectric. IEEE Electron Device Letters, 2019, 40, 1112-1115.	3.9	13
15	Advancements in Solution Processable Devices using Metal Oxides For Printed Internet-of-Things Objects. , 2019, , .		4
16	930 kA/cm ² peak tunneling current density in GaN/AlN resonant tunneling diodes grown on MOCVD GaN-on-sapphire template. Applied Physics Letters, 2019, 114, .	3.3	17
17	2-volt Solution-Processed, Indium Oxide (In ₂ O ₃) Thin Film Transistors on flexible Kapton. , 2019, , .		2
18	New Device Physics of Cross-Gap Electroluminescence in Unipolar-Doped InGaAs/AlAs RTDs. , 2019, , .		1

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19	Pulsed characteristics for high current, large area GaN/AlN resonant tunneling diodes. , 2019, , .		0
20	Polymer solar cells: P3HT:PCBM and beyond. Journal of Renewable and Sustainable Energy, 2018, 10, .	2.0	104
21	431 kA/cm ² peak tunneling current density in GaN/AlN resonant tunneling diodes. Applied Physics Letters, 2018, 112, .	3.3	41
22	Near-UV electroluminescence in unipolar-doped, bipolar-tunneling GaN/AlN heterostructures. Light: Science and Applications, 2018, 7, 17150-17150.	16.6	47
23	Guest Editorial Special Section on the Second Electron Devices Technology and Manufacturing (EDTM) Conference 2018. IEEE Journal of the Electron Devices Society, 2018, 6, 1197-1199.	2.1	0
24	M2M Communication Assessment in Energy-Harvesting and Wake-Up Radio Assisted Scenarios Using Practical Components. Sensors, 2018, 18, 3992.	3.8	5
25	Increasing the Efficiency of Organic Solar Cells by Antireflection Coatings Based on Fluoride Composites. Technical Physics Letters, 2018, 44, 295-296.	0.7	3
26	Negative differential resistance in polymer tunnel diodes using atomic layer deposited, TiO ₂ tunneling barriers at various deposition temperatures. Organic Electronics, 2017, 47, 228-234.	2.6	7
27	Wireless Energy Harvesting and Communications: Limits and Reliability. , 2017, , .		3
28	Viability Bounds of M2M Communication Using Energy-Harvesting and Passive Wake-Up Radio. IEEE Access, 2017, 5, 27868-27878.	4.2	15
29	Feasibility and Fundamental Limits of Energy-Harvesting Based M2M Communications. International Journal of Wireless Information Networks, 2017, 24, 291-299.	2.7	10
30	AlN/GaN/AlN resonant tunneling diodes grown by rf-plasma assisted molecular beam epitaxy on freestanding GaN. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	11
31	Printed and organic diodes: devices, circuits and applications. Flexible and Printed Electronics, 2017, 2, 033001.	2.7	14
32	Antireflection coatings based on fluoride formulations for organic solar cells. Technical Physics Letters, 2016, 42, 359-361.	0.7	4
33	Feasibility and fundamental limits of energy-harvesting based M2M communications. , 2016, , .		6
34	Antireflection composite coatings for organic solar cells. Applied Solar Energy (English Translation) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	1.6	4
35	Highly repeatable room temperature negative differential resistance in AlN/GaN resonant tunneling diodes grown by molecular beam epitaxy. Applied Physics Letters, 2016, 109, .	3.3	52
36	Foreword Special Issue on Advanced Technology for Ultra-Low Power Electronic Devices. IEEE Journal of the Electron Devices Society, 2016, 4, 203-204.	2.1	0

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37	A Nonlinear Circuit Simulation of Switching Process in Resonant-Tunneling Diodes. IEEE Transactions on Electron Devices, 2016, 63, 4993-4997.	3.0	9
38	Experimental determination of quantum-well lifetime effect on large-signal resonant tunneling diode switching time. Applied Physics Letters, 2015, 107, .	3.3	7
39	Tuning the Plasmonic Extinction Resonances of Hexagonal Arrays of Ag Nanoparticles. Plasmonics, 2015, 10, 1505-1512.	3.4	5
40	Anodic Oxidation of Ultra-Thin Ti Layers on ITO Substrates and their Application in Organic Electronic Memory Elements. Electrochimica Acta, 2014, 137, 91-98.	5.2	12
41	Broadband Finite-Difference Time-Domain Modeling of Plasmonic Organic Photovoltaics. ETRI Journal, 2014, 36, 654-661.	2.0	2
42	Towards <i>in vivo</i> biosensors for low-cost protein sensing. Electronics Letters, 2013, 49, 450-451.	1.0	6
43	(Invited) Si/SiGe Resonant Interband Tunnel Diodes Grown by Large-Area Chemical Vapor Deposition. ECS Transactions, 2013, 58, 81-88.	0.5	0
44	Demonstration of hybrid prototype sealant for encapsulating organic photovoltaics. , 2013, , .		0
45	High 5.2 peak-to-valley current ratio in Si/SiGe resonant interband tunnel diodes grown by chemical vapor deposition. Applied Physics Letters, 2012, 100, .	3.3	28
46	200-mm CVD Grown Si/SiGe Resonant Interband Tunnel Diodes Optimized for High Peak-to-Valley Current Ratios. , 2012, , .		0
47	Selective deuteron production using target normal sheath acceleration. Physics of Plasmas, 2012, 19, .	1.9	23
48	Methods for attaining high interband tunneling current in III-Nitrides. , 2012, , .		5
49	Boron Delta-Doping Dependence on Si/SiGe Resonant Interband Tunneling Diodes Grown by Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2012, 59, 602-609.	3.0	11
50	90 nm 32×32 bit Tunneling SRAM Memory Array With 0.5 ns Write Access Time, 1 ns Read Access Time and 0.5 V Operation. IEEE Transactions on Circuits and Systems I: Regular Papers, 2011, 58, 2432-2445.	5.4	16
51	Negative Differential Resistance Devices and Circuits. , 2011, , 176-241.		27
52	Interfacial design and structure of protein/polymer films on oxidized AlGaN surfaces. Journal Physics D: Applied Physics, 2011, 44, 034010.	2.8	9
53	Plasma-polymerized multistacked bipolar gate dielectric for organic thin-film transistors. Organic Electronics, 2010, 11, 1767-1771.	2.6	15
54	Atomic layer deposited HfO ₂ gate dielectrics for low-voltage operating, high-performance poly-(3-hexythiophene) organic thin-film transistors. Organic Electronics, 2010, 11, 1719-1722.	2.6	32

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55	Plasmon-enhanced optical absorption and photocurrent in organic bulk heterojunction photovoltaic devices using self-assembled layer of silver nanoparticles. <i>Solar Energy Materials and Solar Cells</i> , 2010, 94, 128-132.	6.2	195
56	Fabrication of nanowires with high aspect ratios utilized by dry etching with SF ₆ :C ₄ F ₈ and self-limiting thermal oxidation on Si substrate. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 763-768.	1.2	13
57	Zero-bias Si backward diodes detectors incorporating P and B δ-doping layers grown by chemical vapor deposition. , 2009, , .		0
58	Efficient poly(3-hexylthiophene)-fullerene derivative bulk heterojunction photovoltaic devices using unique self-assembled layer of Ag nanoparticles with controllable particle-to-particle spacing. , 2009, , .		0
59	Efficient organic bulk heterojunction solar cells through near infrared absorbing metallated thiophene complexes. , 2009, , .		0
60	Observation of strain in pseudomorphic Si _{1-x} Ge _x by tracking phonon participation in Si ⁺ SiGe resonant interband tunnel diodes via electron tunneling spectroscopy. <i>Journal of Applied Physics</i> , 2009, 106, 034501.	2.5	3
61	P and B doped Si resonant interband tunnel diodes with as-grown negative differential resistance. <i>Electronics Letters</i> , 2009, 45, 759.	1.0	10
62	Si/SiGe Resonant Interband Tunneling Diodes Incorporating δ -Doping Layers Grown by Chemical Vapor Deposition. <i>IEEE Electron Device Letters</i> , 2009, 30, 1173-1175.	3.9	27
63	Plasma-Polymerized Multistacked Organic Bipolar Films: A New Approach to Flexible High- κ Dielectrics. <i>Advanced Materials</i> , 2008, 20, 2383-2388.	21.0	26
64	Surface modification to the indium tin oxide (ITO) anodes through plasma oxidized silver for efficient P3HT:PCBM (1:0.8) bulk heterojunction photovoltaic devices. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008, , .	0.0	0
65	Strain-Engineered Si/SiGe Resonant Interband Tunneling Diodes Grown on $\text{Si}_{0.8}\text{Ge}_{0.2}$ Virtual Substrates With Strained Si Cladding Layers. <i>IEEE Electron Device Letters</i> , 2008, 29, 599-602.	3.9	7
66	Enhanced Emission Using Thin Li-Halide Cathodic Interlayers for Improved Injection into Poly(p-phenylene vinylene) Derivative PLEDs. <i>Electrochemical and Solid-State Letters</i> , 2008, 11, J76.	2.2	5
67	4.8% efficient poly(3-hexylthiophene)-fullerene derivative (1:0.8) bulk heterojunction photovoltaic devices with plasma treated AgO [sub x]/indium tin oxide anode modification. <i>Applied Physics Letters</i> , 2008, 92, 013306.	3.3	47
68	Strain engineered Si ⁺ SiGe resonant interband tunneling diodes with outside barriers grown on Si _{0.8} Ge _{0.2} virtual substrates. <i>Applied Physics Letters</i> , 2008, 93, 102113.	3.3	3
69	Delta-Doped Si/SiGe Zero-Bias Backward Diodes for Micro-Wave Detection. <i>Device Research Conference, IEEE Annual</i> , 2007, , .	0.0	2
70	Temperature dependent empirical modeling of proximity diffused Si esaki diodes and memory circuits. , 2007, , .		0
71	Sensitivity of Si-based zero-bias backward diodes for microwave detection. <i>Electronics Letters</i> , 2007, 43, 295.	1.0	12
72	Anneal time study of Si resonant interband tunnel diodes grown by low-temperature molecular-beam epitaxy. , 2007, , .		0

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73	Simplified Si resonant interband tunnel diodes. , 2007, , .		1
74	Analysis of the Voltage Swing for Logic and Memory Applications in Si/SiGe Resonant Interband Tunnel Diodes Grown by Molecular Beam Epitaxy. IEEE Nanotechnology Magazine, 2007, 6, 158-163.	2.0	8
75	Characterization and Electrical Properties of Individual Au-NiO-Au Heterojunction Nanowires. IEEE Nanotechnology Magazine, 2007, 6, 676-681.	2.0	15
76	NMOS/SiGe Resonant Interband Tunneling Diode Static Random Access Memory. , 2006, , .		9
77	Integration of Si/SiGe HBT and Si-based RITD demonstrating controllable negative differential resistance for wireless applications. Solid-State Electronics, 2006, 50, 973-978.	1.4	11
78	The Effect of Spacer Thicknesses on Si-Based Resonant Interband Tunneling Diode Performance and Their Application to Low-Power Tunneling Diode SRAM Circuits. IEEE Transactions on Electron Devices, 2006, 53, 2243-2249.	3.0	26
79	Si-Based Resonant Interband Tunnel Diode/CMOS Integrated Memory Circuit. , 2006, , .		0
80	Low sidewall damage plasma etching using ICP-RIE with HBr chemistry of Si-SiGe resonant interband tunnel diodes. Electronics Letters, 2006, 42, 719.	1.0	6
81	Pulsed plasma polymerized dichlorotetramethyldisiloxane high-k gate dielectrics for polymer field-effect transistors. Journal of Applied Physics, 2006, 99, 014104.	2.5	6
82	Si/SiGe resonant interband tunnel diode with $f_{\text{sub } r0}$ 20.2 GHz and peak current density 218 kA/cm ² for K-band mixed-signal applications. IEEE Electron Device Letters, 2006, 27, 364-367.	3.9	28
83	Resonant Tunneling and Room Temperature Negative Differential Resistance in TiO ₂ /MEH-PPV Junctions for Quantum Functional Circuits. , 2006, , .		0
84	Phosphorus diffusion in Si-based resonant interband tunneling diodes and tri-state logic using vertically stacked diodes. Materials Science in Semiconductor Processing, 2005, 8, 411-416.	4.0	0
85	RF Performance and Modeling of Si/SiGe Resonant Interband Tunneling Diodes. IEEE Transactions on Electron Devices, 2005, 52, 2129-2135.	3.0	17
86	Temperature dependent DC-RF performance of Si-SiGe resonant interband tunnelling diodes. Electronics Letters, 2005, 41, 559.	1.0	2
87	Room-temperature negative differential resistance in polymer tunnel diodes using a thin oxide layer and demonstration of threshold logic. Applied Physics Letters, 2005, 87, 203506.	3.3	45
88	High-k Polymerized Dichlorotetramethyldisiloxane Films Deposited by Radio Frequency Pulsed Plasma for Gate Dielectrics in Polymer Field Effect Transistors. Materials Research Society Symposia Proceedings, 2005, 870, 131.	0.1	2
89	High sensitivity Si-based backward diodes for zero-biased square-law detection and the effect of post-growth annealing on performance. IEEE Electron Device Letters, 2005, 26, 575-578.	3.9	15
90	Annealing of defect density and excess currents in Si-based tunnel diodes grown by low-temperature molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 747-753.	2.5	17

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91	Three-terminal Si-based negative differential resistance circuit element with adjustable peak-to-valley current ratios using a monolithic vertical integration. Applied Physics Letters, 2004, 84, 2688-2690.	3.3	31
92	High electric-field effects on short-channel polythiophene polymer field-effect transistors. Journal of Applied Physics, 2004, 95, 1497-1501.	2.5	27
93	Radiation tolerance of Si/Si _{0.6} Ge _{0.4} resonant interband tunneling diodes. Journal of Applied Physics, 2004, 95, 6406-6408.	2.5	9
94	Photoresponsivity of polymer thin-film transistors based on polyphenyleneethynylene derivative with improved hole injection. Applied Physics Letters, 2004, 85, 4219-4221.	3.3	60
95	Light Sensitive Polymer Thin Film Transistors Based on BAS-PPE. Materials Research Society Symposia Proceedings, 2004, 814, 152.	0.1	0
96	Improved vertically stacked Si ⁿ -SiGe resonant interband tunnel diode pair with small peak voltage shift and unequal peak currents. Electronics Letters, 2004, 40, 1548.	1.0	6
97	Capacitance-voltage characterization of pulsed plasma polymerized allylamine dielectrics for flexible polymeric field effect transistors. Journal of Electronic Materials, 2004, 33, 1240-1247.	2.2	17
98	Monolithically integrated Si/SiGe resonant interband tunnel diode/CMOS demonstrating low voltage MOBILE operation. Solid-State Electronics, 2004, 48, 1907-1910.	1.4	44
99	Tri-State Logic Using Vertically Integrated Si ⁿ -SiGe Resonant Interband Tunneling Diodes With Double NDR. IEEE Electron Device Letters, 2004, 25, 646-648.	3.9	55
100	Diffusion barrier cladding in Si/SiGe resonant interband tunneling diodes and their patterned growth on PMOS source/drain regions. IEEE Transactions on Electron Devices, 2003, 50, 1876-1884.	3.0	45
101	Growth temperature and dopant species effects on deep levels in Si grown by low temperature molecular beam epitaxy. Journal of Applied Physics, 2003, 93, 9104-9110.	2.5	16
102	151 A/cm ² peak current densities in Si/SiGe resonant interband tunneling diodes for high-power mixed-signal applications. Applied Physics Letters, 2003, 83, 3308-3310.	3.3	38
103	Full band modeling of the excess current in a delta-doped silicon tunnel diode. Journal of Applied Physics, 2003, 94, 5005.	2.5	31
104	Nanometer-period gratings in hydrogen silsesquioxane fabricated by electron beam lithography. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, L12.	1.6	80
105	Capacitance-Voltage Characterization of Pulsed Plasma Polymerized Allylamine Dielectrics. Materials Research Society Symposia Proceedings, 2002, 736, 1.	0.1	0
106	Growth Temperature Effects on Deep-Levels in Si Grown by Low Temperature Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 745, 691.	0.1	0
107	Metal-semiconductor-metal photodetectors. , 2001, 4285, 198.		14
108	œp-on-n-Si interband tunnel diode grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 290.	1.6	15

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109	pnp Si resonant interband tunnel diode with symmetrical NDR. Electronics Letters, 2001, 37, 1412.	1.0	9
110	Full-band simulation of indirect phonon assisted tunneling in a silicon tunnel diode with delta-doped contacts. Applied Physics Letters, 2001, 78, 814-816.	3.3	60
111	Epitaxial Si-based tunnel diodes. Thin Solid Films, 2000, 380, 145-150.	1.8	16
112	Current-voltage characteristics of high current density silicon Esaki diodes grown by molecular beam epitaxy and the influence of thermal annealing. IEEE Transactions on Electron Devices, 2000, 47, 1707-1714.	3.0	47
113	Epitaxially grown Si resonant interband tunnel diodes exhibiting high current densities. IEEE Electron Device Letters, 1999, 20, 329-331.	3.9	30
114	Strain modification in thin $\text{Si}_{1-x}\text{Ge}_x$ alloys on (100) Si for formation of high density and uniformly sized quantum dots. Journal of Applied Physics, 1999, 85, 578-582.	2.5	12
115	Si resonant interband tunnel diodes grown by low-temperature molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 1308-1310.	3.3	29
116	<title>Optically interconnected static RAM for instruction-level parallel processors</title>. , 1999, , .		0
117	Electrical and optical properties of phosphorus doped $\text{Ge}_{1-x}\text{Si}_x$. Thin Solid Films, 1998, 321, 47-50.	1.8	0
118	Room temperature operation of epitaxially grown Si/Si _{0.5} Ge _{0.5} /Si resonant interband tunneling diodes. Applied Physics Letters, 1998, 73, 2191-2193.	3.3	104
119	1.3 μm photoresponsivity in Si-based $\text{Ge}_{1-x}\text{Si}_x$ photodiodes. Applied Physics Letters, 1998, 72, 1860-1862.	3.3	25
120	Photoluminescence Of $\text{Si}_{1-x}\text{Ge}_x$ Alloys Grown On (100) Si Substrates. Materials Research Society Symposia Proceedings, 1998, 533, 327.	0.1	1
121	$\text{Ge}_{1-x}\text{Si}_x$ /Si heterojunction photodiode. , 1997, 3007, 162.		0
122	<title>Equivalent circuit modeling of metal-semiconductor-metal photodiodes with transparent conductor electrodes</title>. , 1997, , .		1
123	A p- $\text{Ge}_{1-x}\text{C}_x$ /n-Si heterojunction diode grown by molecular beam epitaxy. IEEE Electron Device Letters, 1997, 18, 411-413.	3.9	5
124	Low resistance ohmic contacts to p- $\text{Ge}_{1-x}\text{C}_x$ on Si. IEEE Electron Device Letters, 1997, 18, 7-9.	3.9	4
125	Near band edge photoluminescence from pseudomorphic tensially strained $\text{Si}_{0.985}\text{C}_{0.015}$ alloy. Thin Solid Films, 1997, 294, 122-124.	1.8	2
126	In _{0.53} Ga _{0.47} As MSM photodiodes with transparent CTO Schottky contacts and digital superlattice grading. IEEE Transactions on Electron Devices, 1997, 44, 2174-2179.	3.0	23

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127	Band-edge photoluminescence from pseudomorphic Si _{0.96} Sn _{0.04} alloy. Applied Physics Letters, 1996, 68, 3105-3107.	3.3	20
128	MSM photodiodes. IEEE Potentials, 1996, 15, 25-29.	0.3	26
129	Current transport characteristics of SiGeC/Si heterojunction diode. IEEE Electron Device Letters, 1996, 17, 589-591.	3.9	10
130	Liquid-phase epitaxial growth process of InGaAs on InP with rare-earth treatment. , 1996, , .		0
131	Optical properties of Ge _{1-y} Cy alloys. Journal of Electronic Materials, 1996, 25, 297-300.	2.2	27
132	Realization of in-situ sub two-dimensional quantum structures by strained layer growth phenomena in the In _x Ga _{1-x} As/GaAs system. Journal of Electronic Materials, 1996, 25, 479-483.	2.2	14
133	Liquid phase epitaxial growth of InGaAs on InP using rare-earth-treated melts. Journal of Applied Physics, 1996, 80, 7094-7103.	2.5	27
134	Optical and electronic properties of SiGeC alloys grown on Si substrates. Journal of Crystal Growth, 1995, 157, 386-391.	1.5	45
135	Transparent and opaque Schottky contacts on undoped In _{0.52} Al _{0.48} As grown by molecular beam epitaxy. Applied Physics Letters, 1995, 66, 3471-3473.	3.3	33
136	In _{0.53} Ga _{0.47} As metal-semiconductor-metal photodiodes with transparent cadmium tin oxide Schottky contacts. Applied Physics Letters, 1994, 65, 1930-1932.	3.3	43
137	<title>Monolithic p-i-n-FET photoreceivers</title>. , 1994, 2149, 414.		0
138	Monolithic GaAs/AlGaAs optical transmitter circuit using a single growth step. Electronics Letters, 1994, 30, 490-491.	1.0	3
139	8-element linear array monolithic p-i-n MODFET photoreceivers using molecular beam epitaxial regrowth. IEEE Photonics Technology Letters, 1993, 5, 63-66.	2.5	7
140	Monolithic GaAs/AlGaAs pin MESFET photoreceiver using a single molecular beam epitaxy growth step. Electronics Letters, 1993, 29, 1133.	1.0	3
141	Substrate orientation effects on dopant incorporation in InP grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1993, 73, 4095-4097.	2.5	19
142	10 GHz bandwidth monolithic modulated doped field effect transistor photoreceiver. Applied Physics Letters, 1993, 63, 2115-2116.	3.3	13
143	In _{0.53} Ga _{0.47} As photodiodes with transparent cadmium tin oxide contacts. Applied Physics Letters, 1992, 61, 1673-1675.	3.3	10
144	<title>Buried heterostucture lasers using a single-step metal-organic chemical vapor deposition growth over patterned substrates</title>. , 1992, 1676, 117.		2

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145	1.0 GHz monolithic p-n MODFET photoreceiver using molecular beam epitaxial regrowth. IEEE Photonics Technology Letters, 1992, 4, 891-894.	2.5	9
146	A waveguide directional coupler with a nonlinear coupling medium. IEEE Journal of Quantum Electronics, 1991, 27, 788-795.	1.9	28
147	Effects of substrate tilting in substantial improvement of DC performance of AlGaAs/GaAs n-p-n DHBTs grown by MBE. IEEE Transactions on Electron Devices, 1991, 38, 2717-2718.	3.0	0
148	Monolithically integrated InP-based front-end photoreceivers. IEEE Transactions on Electron Devices, 1991, 38, 1324-1333.	3.0	31
149	Performance characteristics of GaInAs/GaAs large optical cavity quantum well lasers. Electronics Letters, 1991, 27, 680.	1.0	18
150	An AlGaAs double-heterojunction bipolar transistor grown by molecular beam epitaxy. Applied Physics Letters, 1991, 59, 1099-1101.	3.3	7
151	Substantial improvement by substrate misorientation in dc performance of Al _{0.5} Ga _{0.5} As/GaAs/Al _{0.5} Ga _{0.5} As double-heterojunction NpN bipolar transistors grown by molecular beam epitaxy. Applied Physics Letters, 1991, 59, 186-188.	3.3	11
152	Monolithic integration of GaAs and In _{0.2} Ga _{0.8} As lasers by molecular beam epitaxy on GaAs. Applied Physics Letters, 1991, 58, 2698-2700.	3.3	5
153	Monolithically Peltier-cooled vertical-cavity surface-emitting lasers. Applied Physics Letters, 1991, 59, 117-119.	3.3	37
154	GaAs quantum well laser and heterojunction bipolar transistor integration using molecular beam epitaxial regrowth. Applied Physics Letters, 1991, 59, 2826-2828.	3.3	12
155	The relation of the performance characteristics of pseudomorphic In _{0.53+x} Ga _{0.47-x} As/In _{0.52} Al _{0.48} As (0 ≤ x ≤ 0.32) modulation-doped field-effect transistors to molecular beam epitaxial growth modes. Journal of Applied Physics, 1990, 68, 347-350.	2.5	28
156	Investigation of the interface region produced by molecular beam epitaxial regrowth. Journal of Electronic Materials, 1989, 18, 137-142.	2.2	24
157	Growth phenomena and characteristics of strained In _x Ga _{1-x} As on GaAs. Journal of Crystal Growth, 1989, 95, 193-196.	1.5	4
158	Recombination velocity at molecular beam epitaxial GaAs regrown interfaces. Journal of Applied Physics, 1989, 65, 2571-2573.	2.5	6
159	Role of strain and growth conditions on the growth front profile of In _x Ga _{1-x} As on GaAs during the pseudomorphic growth regime. Applied Physics Letters, 1988, 53, 684-686.	3.3	246
160	Demonstration of all-optical modulation in a vertical guided-wave nonlinear coupler. Applied Physics Letters, 1988, 52, 1125-1127.	3.3	28
161	Orientation-dependent phase modulation in InGaAs/GaAs multi-quantum well waveguides. Applied Physics Letters, 1988, 53, 2129-2131.	3.3	15
162	In-Situ RHEED Studies To Understand The Dislocation Formation Process In Growth Of InGaAs on GaAs. , 1988, 0944, 10.		0

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163	A study of strain-related effects in the molecular-beam epitaxy growth of $\text{In}_x\text{Ga}_{1-x}\text{As}$ on GaAs using reflection high-energy electron diffraction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1162.	1.6	40
164	Comparative study of the growth processes of GaAs, AlGaAs, InGaAs, and InAlAs lattice matched and nonlattice matched semiconductors using high-energy electron diffraction. Journal of Applied Physics, 1987, 61, 2856-2860.	2.5	41
165	Molecular beam epitaxial growth and luminescence of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{In}_x\text{Al}_{1-x}\text{As}$ multiquantum wells on GaAs. Applied Physics Letters, 1987, 51, 261-263.	3.3	8
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